

## HiPerFET™ Power MOSFET

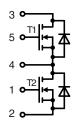
Phaseleg Topology in ISOPLUS i4-PAC™

= 75 A= 100 V $R_{DSontyp.} = 18 \text{ m}\Omega$ 

Preliminary data

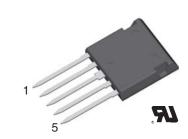
 $\mathbf{E}_{\mathrm{AR}}$ 

 $T_C = 25^{\circ}C$ 



30

mJ



MOSFET T1/T2			
Conditions	Maximum Ratings		
$T_{VJ} = 25^{\circ}C$ to $150^{\circ}C$	100	V	
	±20	V	
$T_{C} = 25^{\circ}C$ $T_{C} = 90^{\circ}C$	75 50	A A	
(body diode) $T_C = 25^{\circ}C$ (body diode) $T_C = 90^{\circ}C$	100 60	A A	
$V_{DS} < V_{DSS}; I_F \le 300A; \mid di_F/dt \mid \le 100A/\mu s; R_G = 2 \Omega T_{VJ} = 150^{\circ}C$	2 5	V/ns	
	Conditions $T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$ $T_{C} = 25^{\circ}\text{C}$ $T_{C} = 90^{\circ}\text{C}$ (body diode) $T_{C} = 25^{\circ}\text{C}$ (body diode) $T_{C} = 90^{\circ}\text{C}$ $V_{DS} < V_{DSS}; I_{F} \le 300\text{A};  di_{F}/dt  \le 100\text{A}/\mu\text{s}; R_{G} = 2.5^{\circ}\text{C}$		

Symbol	Conditions		Characteristic Values (T <sub>VI</sub> = 25°C, unless otherwise specified)	
		min.	typ.	max.

R <sub>DSon</sub>	$V_{GS} = 10 \text{ V}; I_D = I_{D90}$	18	25 mΩ
V <sub>GSth</sub>	$V_{DS} = 20 \text{ V}; I_D = 4 \text{ mA}$ 2		4 V
I <sub>DSS</sub>	$V_{DS} = V_{DSS}$ ; $V_{GS} = 0 \text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.25	0.3 mA mA
I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$		200 nA
$egin{array}{c} oldsymbol{Q}_{g} \ oldsymbol{Q}_{gs} \ oldsymbol{Q}_{gd} \end{array}$	$ V_{GS} = 10 \text{ V}; V_{DS} = 0.5 \bullet V_{DSS}; I_{D} = I_{D90} $	180 35 85	nC nC nC
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	$\begin{cases} V_{GS} = 10 \text{ V}; V_{DS} = 0.5 \bullet V_{DSS} \\ I_{D} = I_{D90}; R_{G} = 2 \Omega \end{cases}$	20 60 80 60	ns ns ns ns
V <sub>F</sub>	(body diode) I <sub>F</sub> = 75 A; V <sub>GS</sub> = 0 V	1.2	1.5 V
t <sub>rr</sub>	(body diode) $I_F = 37.5A$ ; -di/dt = 100A/ $\mu$ s; $V_{DS} = 25V$	300	ns
R <sub>thJC</sub> R <sub>thJH</sub>	with heat transfer paste	0.93	0.5 K/W K/W

## **Features**

- HiPerFET™ technology
- low  $\mathbf{R}_{\mathrm{DSon}}$  low gate charge for high frequency operation
- unclamped inductive switching (UIS) capability
- dv/dt ruggedness
- fast intrinsic reverse diode
- ISOPLUS i4-PAC<sup>™</sup> package
- isolated back surface
- low coupling capacity between pins and heatsink
- enlarged creepage towards heatsink
- application friendly pinout
- low inductive current path
- high reliability
- industry standard outline
- UL registered E 72873

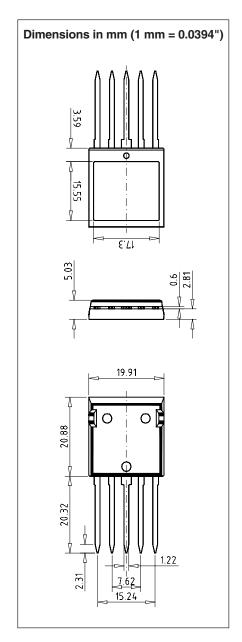
## **Applications**

- drives and power supplies
- battery or fuel cell powered
- automotive, industrial vehicle etc.
- secondary side of mains power supplies



Component				
Symbol	Conditions	Maximum Ratings		
T <sub>VJ</sub> T <sub>stg</sub>		-55+150 -55+125	°C	
V <sub>ISOL</sub>	I <sub>ISOL</sub> ≤ 1 mA; 50/60 Hz	2500	٧~	
F <sub>c</sub>	mounting force with clip	20120	N	

Symbol	Conditions	Ch	Characteristic Values	
		min.	typ.	max.
C <sub>p</sub>	coupling capacity between shorted pins and mounting tab in the case		40	pF
d <sub>s</sub> ,d <sub>A</sub> d <sub>s</sub> ,d <sub>A</sub>	pin - pin pin - backside metal	1.7 5.5		mm mm
Weight			9	g



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